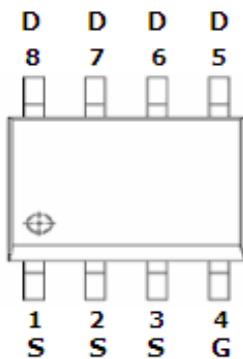


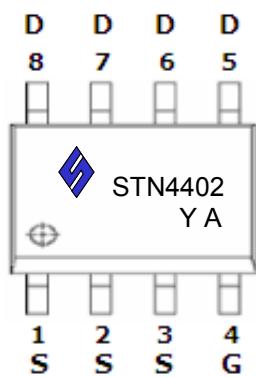
DESCRIPTION

STN4402 is the N-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as power management and other battery powered circuits where high-side switching.

PIN CONFIGURATION SOP-8

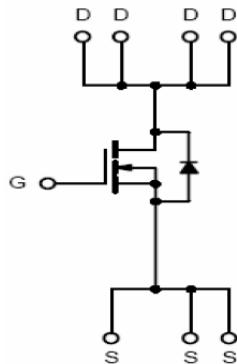


PART MARKING SOP-8



FEATURE

- 30V/12A, $R_{DS(ON)} = 13m\Omega$ (Typ.)
@ $V_{GS} = 10V$
- 30V/10A, $R_{DS(ON)} = 18m\Omega$
@ $V_{GS} = 4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP-8 package design



Y: Year Code A: Process Code



STN4402 Pb
Lead-free

N Channel Enhancement Mode MOSFET

12A

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	VDSS	30	V
Gate-Source Voltage	VGSS	±20	V
Continuous Drain Current (TJ=150°C)	ID	12 10	A
Pulsed Drain Current	IDM	30	A
Continuous Source Current (Diode Conduction)	IS	2.3	A
Power Dissipation	PD	2.5 1.6	W
Operation Junction Temperature	TJ	-55/150	°C
Storage Temperature Range	TSTG	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	80	°C/W



STN4402 Pb Lead-free

N Channel Enhancement Mode MOSFET

12A

ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

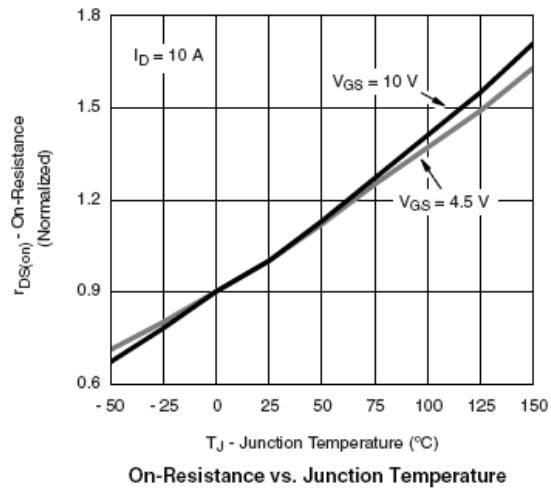
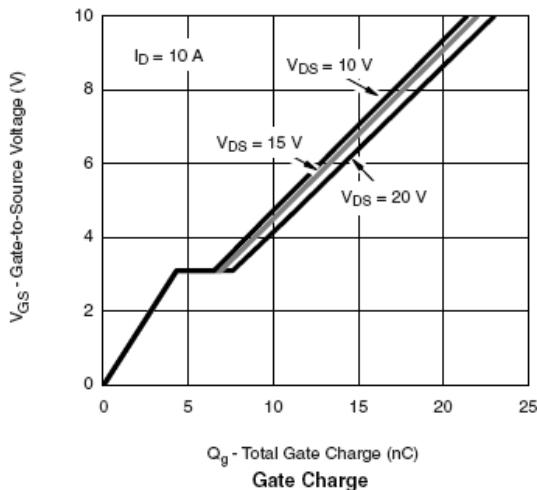
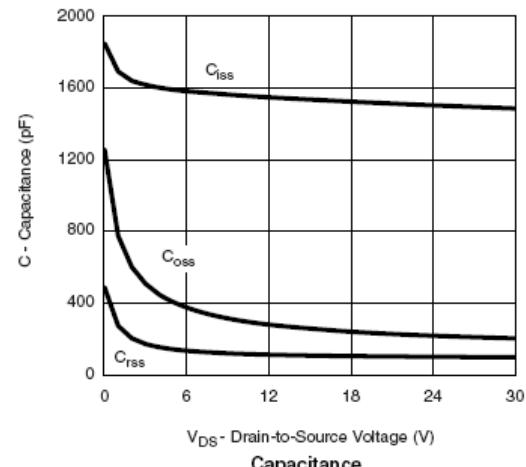
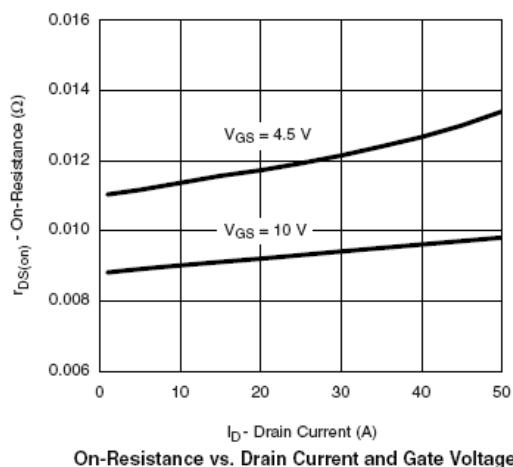
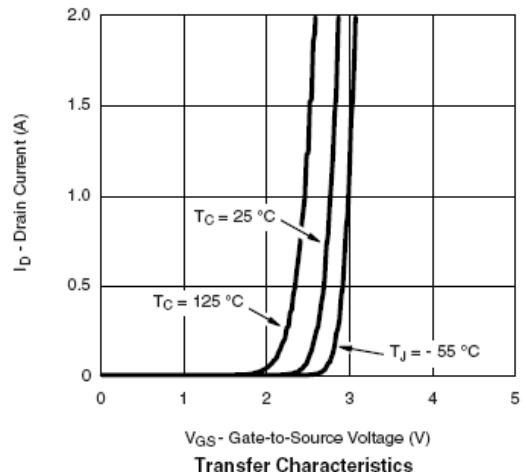
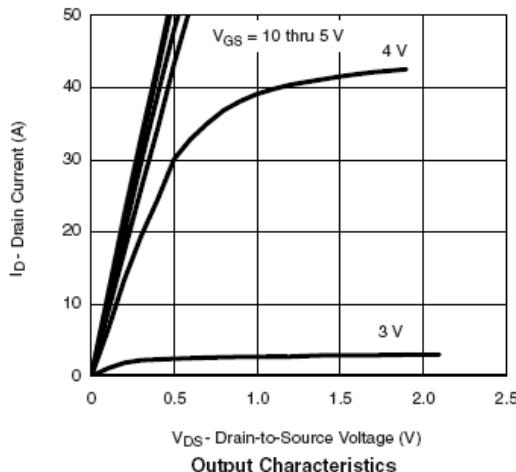
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, ID=250uA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , ID=250uA	1.0		3.0	V
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =24V, V _{GS} =0V			1	uA
		V _{DS} =24V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥5V, V _{GS} =10V	25			A
Drain-source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A V _{GS} =4.5V, I _D =10A		10 13	13 18	mΩ
Forward Transconductance	g _{fs}	V _{DS} =15V, I _D =6.2AV		13		S
Diode Forward Voltage	V _{SD}	I _s =2.3A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =15V, V _{GS} =10V I _D =2A		16	24	nC
Gate-Source Charge	Q _{gs}			4.2		
Gate-Drain Charge	Q _{gd}			2.5		
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} =0V F=1MHz		1350		pF
Output Capacitance	C _{oss}			258		
Reverse TransferCapacitance	C _{rss}			150		
Turn-On Time	t _{d(on)} tr	V _{DD} =15V, R _L =15Ω I _D =5.0A, V _{GEN} =-10V R _G =1Ω		15	20	nS
				6	16	
Turn-Off Time	t _{d(off)} tf			20	40	
				12	20	

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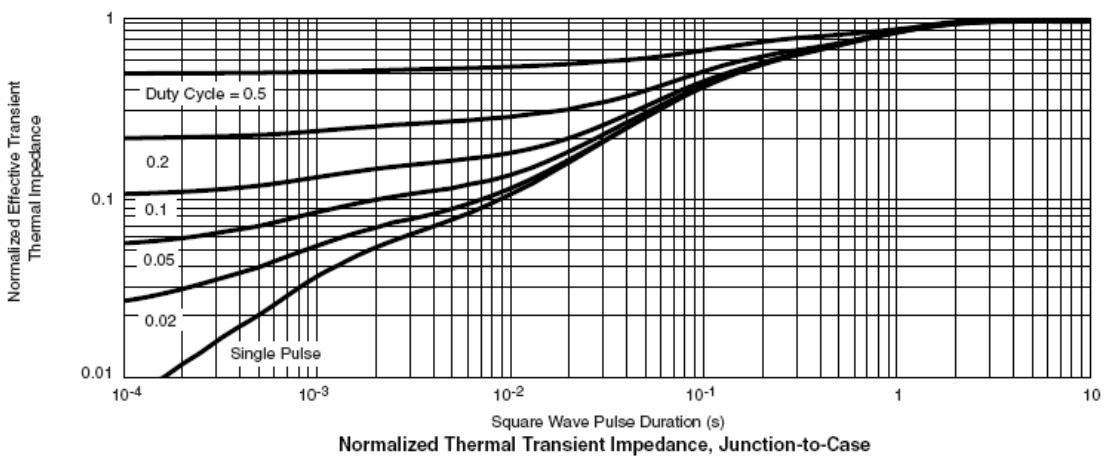
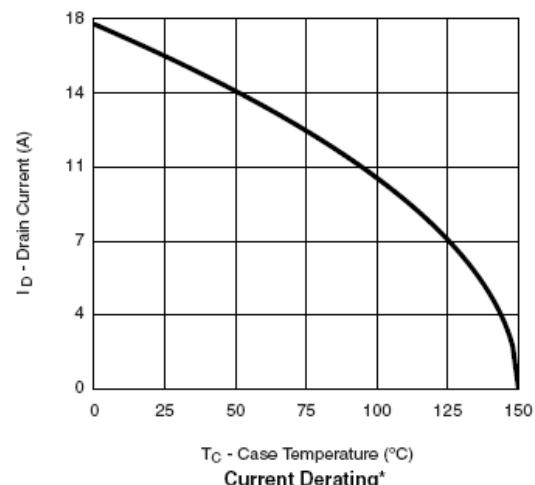
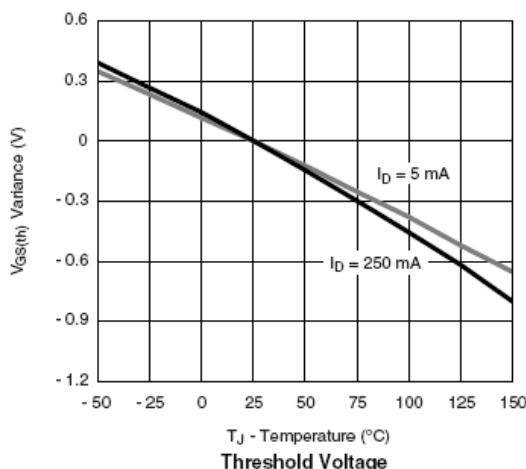
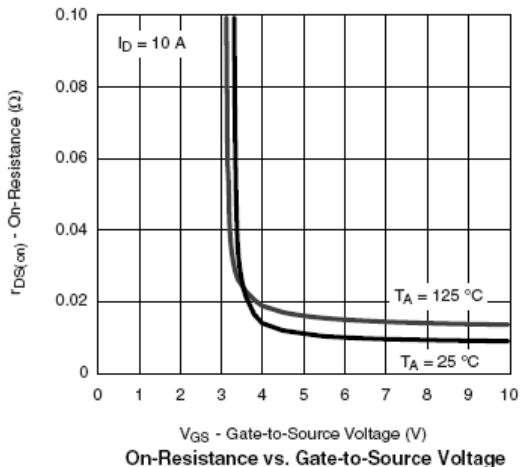
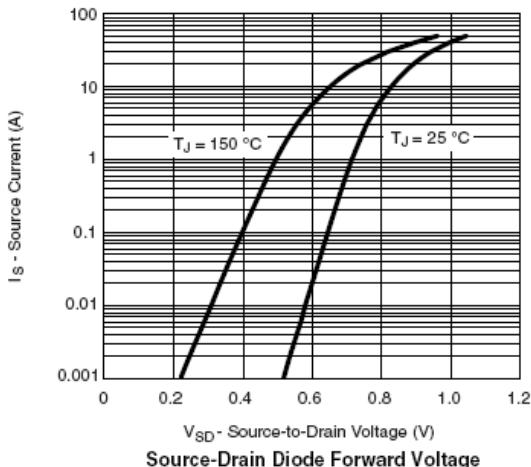
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TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



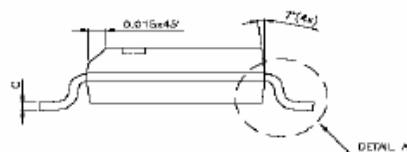
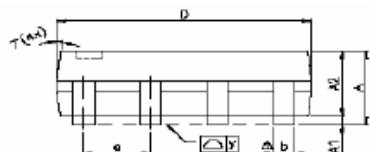
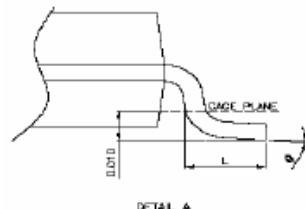
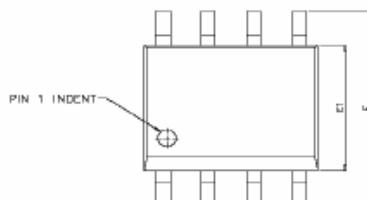


STN4402 Pb Lead-free

N Channel Enhancement Mode MOSFET

12A

PACKAGE OUTLINE SOP-8P



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δy	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°

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